

## 上海奥普特科晶体材料有限公司 Shanghai Opticrystal Materials Co., Ltd

InP indium phosphide :

As one of the most important compound semiconductor materials, InP indium phosphide single crystal material is the key material for the production of InP-based laser diodes (LDs), light-emitting diodes (LEDs) and photodetectors in optical communications. These devices realize optical fiber communications. Information transmission, dissemination, amplification, reception and other functions.

InP is also very suitable for high-frequency devices, such as high electron mobility transistor (HEMT) and heterojunction bipolar transistor (HBT), etc. Due to its superior characteristics, it is used in optical fiber communication, microwave, millimeter wave, anti- Radiation solar cells, heterojunction transistors and many other high-tech fields have a wide range of applications.

The main growth methods of InP single crystal materials include traditional liquid seal Czochralski technology (LEC), improved LEC technology, gas pressure controlled Czochralski technology (VCZ/PC-LEC)/vertical gradient solidification technology (VGF)/vertical bridge Man Technology (VB), etc.

single	doping	conductivity	Carrier	Mobility	Dislocation	standard
InP	Intrinsic	Ν	(0.4-2) x 10 16	(3.5-4) x 10 <sup>3</sup>	<b>£</b> 5 x 10 <sup>4</sup>	Φ2"×0.35mm
InP	S	N	(0.8-3) x 10 <sup>18</sup> (4-6)'10 <sup>18</sup>	(2.0-2.4) x 10 3 (1.3-1.6) x 10	<b>£</b> 3 x 10 <sup>4</sup> <b>£</b> 2 x 10 <sup>3</sup>	Φ2"×0.35mm Φ3"×0.35mm
InP	Zn	Р	(0.6-2) x 10 <sup>18</sup>	70-90	<b>£</b> 2 x 10 <sup>4</sup>	Φ2"×0.35mm
InP	Te	Ν	107-10 8	<sup>3</sup> 2000	<b>£</b> 3 x 10 <sup>4</sup>	Φ2"×0.35mm
Dimensions (mm)			Dia50.8x0.35mm, 10×10×0.35mm, 10×5×0.35mm can be customized			
structure			Cubic, a=5.869 A			
crystal direction			<100>			
melting point			1600°C			
density			4.79 g/ cm3			
Bandgap width			1.344			
Surface roughness			Ra:≦ 1nm			
polishing			single or double sided			
Package			Class 100 clean bag, Class 1000 ultra-clean room			

## **Product parameters:**